



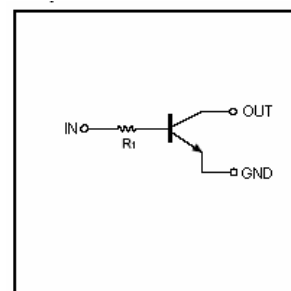
TIGER ELECTRONIC CO.,LTD

Digital transistors (built-in resistors)

DTC143TM/DTC143TE/DTC143TUA DTC143TKA /DTC143TSA/ DTC143TCA

DIGITAL TRANSISTOR (NPN)

Equivalent Circuit

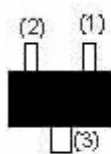


FEATURES

1. Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors(see equivalent circuit)
2. The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input.They also have the advantage of almost completely eliminating parasitic effects
3. Only the on/off conditions need to be set for operation, making device design easy

PIN CONNENCTIONS AND MARKING

DTC143TE



1.IN
2.GND
3.OUT

SOT-523

Abbreviated symbol: 03

DTC143TUA

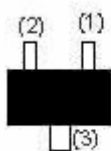


1.IN
2.GND
3.OUT

SOT-323

Abbreviated symbol: 03

DTC143TKA



1.IN
2.GND
3.OUT

SOT-23-3L

Abbreviated symbol: 03

DTC143TCA

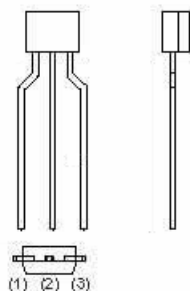


1.IN
2.GND
3.OUT

SOT-23

Abbreviated symbol: 03

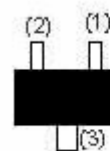
DTC143TSA



1.GND
2.OUT
3.IN

TO-92S

DTC143TM



1.IN
2.GND
3.OUT

SOT-723

Abbreviated symbol: 03

Absolute maximum ratings(Ta=25°C)

Parameter	Symbol	Limits (DTC143T□)						Unit
		M	E	UA	CA	KA	SA	
Collector-base voltage	V _{(BR)CBO}	50						V
Collector-emitter voltage	V _{(BR)CEO}	50						V
Emitter-base voltage	V _{(BR)EBO}	5						V
Collector current	I _C	100						mA
Collector Power dissipation	P _C	100	150	200			300	mW
Junction temperature	T _j	150						℃
Storage temperature	T _{stg}	-55~150						℃

Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Collector-base breakdown voltage	$V_{(BR)CBO}$	50			V	$I_C=50\mu A$
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	50			V	$I_C=1mA$
Emitter-base breakdown voltage	$V_{(BR)EBO}$	5			V	$I_E=50\mu A$
Collector cut-off current	I_{CBO}			0.5	μA	$V_{CB}=50V$
Emitter cut-off current	I_{EBO}			0.5	μA	$V_{EB}=4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$			0.3	V	$I_C=5mA, I_B=0.25mA$
DC current transfer ratio	h_{FE}	100		600		$V_{CE}=5V, I_C=1mA$
Input resistance	R_1	3.29	4.7	6.11	K Ω	
Transition frequency	f_T		250		MHz	$V_O=10V, I_O=5mA, f=100MHz$